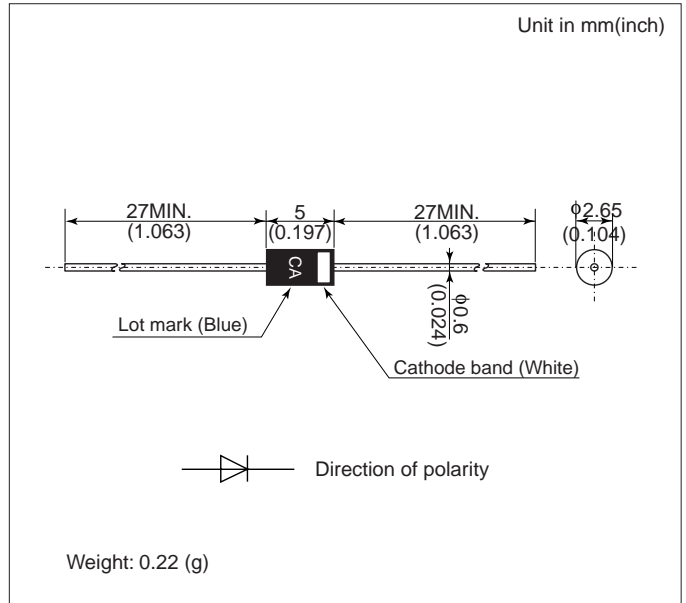


# DHM3S20

## FEATURES

- High voltage rectification for office equipment.
- Diffused-junction.
- Excellent high temperature output characteristics ( Small leakage current at high temperature and excellent reverse characteristics )

## OUTLINE DRAWING



## ABSOLUTE MAXIMUM RATINGS

Item	Type		DHM3S20
Repetitive Peak Reverse Voltage*	$V_{RRM}$	kV	2
Non-Repetitive Peak Reverse Voltage*	$V_{RSM}$	kV	2.5
Average Forward Current	$I_{F(AV)}$	mA	3 ( 15.75kHz C-Load )
Surge(Non-Repetitive) Forward Current	$I_{FSM}$	A	0.5
Operating Junction Temperature	$T_j$	°C	-40 ~ +120
Storage Temperature	$T_{stg}$	°C	-40 ~ +120

## CHARACTERISTICS ( $T_C=25^\circ\text{C}$ unless otherwise specified)

Item	Symbols	Units	Min.	Typ.	Max.	Test Conditions
Peak Reverse Current*	$I_{RRM}$	$\mu\text{A}$	—	—	2.0	$V_R = V_{RRM}$
Peak Forward Voltage	$V_{FM}$	V	—	—	10	$I_{FM} = 5\text{mA}$
Reverse Recovery Time	$t_{rr}$	ns	—	—	100	$I_F = 2\text{mA}$ , $I_{RP} = 5\text{mA}$ , 1mA recovery

Notes \*Diode tested in adequate thermal and dielectric medium.

# HITACHI POWER SEMICONDUCTORS

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